

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-20: (Canceled)

21. (Previously presented): A system for an apparatus of the type adapted to treat substrates and/or wafers, the system comprising a stationary base element and a movable support for at least one substrate or at least one wafer, the support being rotatable above the element about a stationary axis, a chamber being provided, defined between the element and the support, at least one duct being provided for the admission of at least one gas-flow to the chamber in order to raise the support, the system comprising means for converting the flow of gas into the chamber into rotation of the support, said means comprising a plurality of channels each of which is defined between the element and the support and is in communication with the chamber, and each of which has a shape and size such that the gas that is present in the chamber, as a result of inward flow of the gas, flows through the channels as a result of pressure in the chamber and causes the support to rotate as a result of fluid-dynamic drive characterized in that each of said channels has a depth that gradually reduces along its extent.

22. (Previously presented): A system according to Claim 21, in which the chamber is substantially closed both when the support is stationary and when the support is in motion.

23. (Previously presented): A system according to Claim 21, in which said means comprise at least one duct outlet for a gas-flow, in which said outlet opens into the chamber and is configured in a manner such that the emerging gas-flow is skew relative to the axis of rotation of the support.

24. (Previously presented): A system according to Claim 23, in which said means comprise two duct outlets for two gas-flows, in which said outlets open into the chamber in

positions that are preferably symmetrical with respect to the axis of rotation of the support and are configured in a manner such that the two emerging gas-flows are skew and preferably symmetrical with respect to the axis of rotation of the support.

25. (Previously presented): A system according to Claim 21, in which said means comprise at least one duct outlet for a gas-flow, in which said outlet opens into the chamber and is configured in a manner such that the emerging gas-flow is substantially parallel to the axis of rotation of the support.

26. (Previously presented): A system according to Claim 25, in which said means comprise two duct outlets for two gas-flows, in which said outlets open into the chamber in positions that are preferably symmetrical with respect to the axis of rotation of the support and the outlets are configured in a manner such that the two emerging gas-flows are substantially parallel to the axis of rotation of the support.

27. (Previously presented): A system according to Claim 25, in which the surface of the support which delimits the chamber is shaped in a manner such that a gas-flow parallel to the axis of rotation of the support transmits a tangential force to the support.

28-30. (Canceled)

31. (Previously presented): A system according to Claim 21, in which the chamber has a substantially cylindrical shape and the channels are substantially straight and tangential to the profile of the chamber.

32. (Previously presented): A system according to Claim 21, in which the chamber is formed entirely in the element.

33. (Previously presented): A system according to Claim 21, in which the channels are formed entirely in the element.

34. (Previously presented): A system according to Claim 32, in which the element has a circular recess adapted to house the support rotatably, in which the chamber is formed in the element in a central zone of the recess, and in which the channels are formed in the element in a peripheral zone of the recess.

35. (Previously presented): A system according to Claim 21, in which a pin/hole pair is provided on the element/support pair, for the mechanical restraint of the rotation of the support above the element.

36. (Previously presented): A system according to Claim 21, characterized in that it is substantially symmetrical with respect to the axis of rotation of the support.

37. (Previously presented): A system according to Claim 21, in which the element is adapted to constitute a slide of a treatment chamber of a treatment apparatus.

38. (Previously presented): A system according to Claim 21, in which the support is adapted to also act as a susceptor.

39. (Previously presented): A reactor for the epitaxial growth of semiconductor materials on substrates, characterized in that it comprises a support system for substrates according to Claim 21.

40. (Previously presented): An apparatus for the thermal treatment of wafers at high temperature, characterized in that it comprises a support system for wafers according to Claim 21.

41. (Previously presented): A system according to Claim 33, wherein each of the channels has a maximum depth and a minimum depth, wherein the maximum depth of at least one of the channels is more centrally located in the element than the minimum depth of the at least one channel.

42. (Previously presented): A system according to Claim 41, wherein the maximum depths of the channels are more centrally located in the element than the minimum depths of the channels.

43. (New): A system for an apparatus of the type adapted to treat substrates and/or wafers, the system comprising a stationary base element and a movable support for at least one substrate or at least one wafer, the support being rotatable above the element about a stationary axis, a chamber being provided, defined between the element and the support, at least one duct being provided for the admission of at least one gas-flow to the chamber in order to raise the support, the system comprising means for converting the flow of gas into the chamber into rotation of the support, said means comprising a plurality of channels each of which is defined between the element and the support, each of the channels extending from the chamber and terminating short of an outer groove of the stationary base element, each channel having a shape and size such that the gas that is present in the chamber, as a result of inward flow of the gas, flows through the channels as a result of pressure in the chamber and causes the support to rotate as a result of fluid-dynamic drive characterized in that each of said channels has a depth that gradually reduces along its extent.